

ABSTRACT

A semiconductor device and a method for fabricating the semiconductor device are provided. The semiconductor device includes: a substrate including a cell area, a first peripheral circuit area disposed adjacent to the cell area in a first direction, and a second peripheral circuit area disposed adjacent to the cell area in a second direction intersecting with the first direction; first lower conductive lines disposed over the substrate, extending in the first direction; first memory cells disposed in intersection regions between the first lower conductive lines and the first segments of the first upper conductive patterns; second lower conductive lines extending in the second direction and disposed over the first upper conductive patterns; second upper conductive lines disposed over the second lower conductive lines, extending in the first direction, and crossing both the cell area and the first peripheral circuit area; and second memory cells disposed in intersection regions between the second lower conductive lines and the second upper conductive lines.

FIG. 6A